

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	2	("20030013266").pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 18:05
S1	7170	(first or second) near3 (form\$3 near3 (underly\$3 layer or mask) same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 10:07
S2	7293	((first or second or third or fourth or fifth or sixth or seventh) near3 process) same (form\$3 near3 (underly\$3 layer or mask) or (bump and dip near3 transfer layer) or ((planar\$3 or light absor\$3 or light-emit\$3 or light emit\$3) near3 layer)same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 10:59
S3	1367	S1 and S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 10:59
S4	67	S3 and ((first second third fourth fifth sixth seventh) near3 process)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/27 11:07
S5	7	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/27 10:58
S6	4	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/27 10:58

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S7	0	S4 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 18:05
S8	71	S4 or S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 11:06
S9	67	S8 and (((first or second or third or fourth or fifth or sixth or seventh) near\$3 process) same (form\$3 near\$3 (underly\$3 layer or mask) or (bump and dip near\$3 transfer layer) or ((planar\$3 or light absor\$3 or light-emit\$3 or light emit\$3) near\$3 layer)same substrate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 11:00
S10	71	S8 and (first second third fourth fifth sixth seventh process planar\$3 layer form\$3 microscopic plane decompos\$3 transfer\$3 extract\$3 active substrate light absor\$3 emit\$3 grow\$3 irradiat\$3 nitride n-type p-type type semiconductor wafer sapphire GaN AlN SiC principal plane nitrogen crystal\$3 groove\$3 cut\$3 gap energy band level impur\$3 pur\$3 radiat\$3 non-radiat\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/27 11:15